

SI2337DS-T1-GE3-VB Datasheet

-60V Trench Single-P SOT23-3 MOSFET

PRODUCT SUMMARY

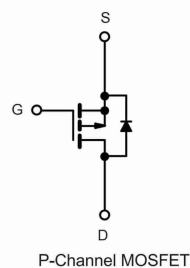
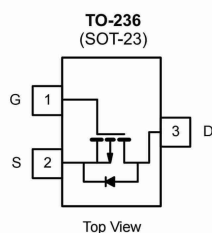
V_{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I_D (A) ^d	Q_g (TYP.)
-60	0.070 at $V_{GS} = -10$ V	-4.5	10.1 nC
	0.085 at $V_{GS} = -4.5$ V	-4.0	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	-4.5	A
	$T_C = 70$ °C		-4.0	
	$T_A = 25$ °C		-3.5 ^{a,b}	
	$T_A = 70$ °C		-3.0 ^{a,b}	
Pulsed Drain Current ($t = 100$ μ s)		I_{DM}	-20	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	-3.9	
	$T_A = 25$ °C		-2.1 ^{a,b}	
Avalanche Current		I_{AS}	-15	mJ
Single-Pulse Avalanche Energy		E_{AS}	11.25	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	4.2	W
	$T_C = 70$ °C		2.7	
	$T_A = 25$ °C		2 ^{a,b}	
	$T_A = 70$ °C		1.3 ^{a,b}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	$t \leq 5$ s	R_{thJA}	100	130	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJF}	60	75	

Notes

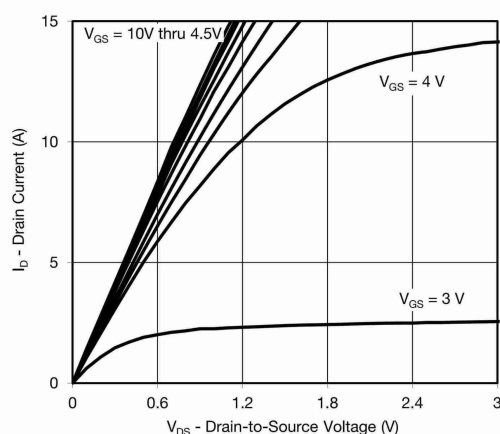
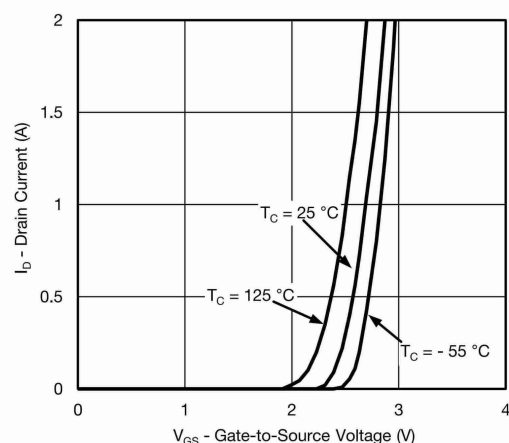
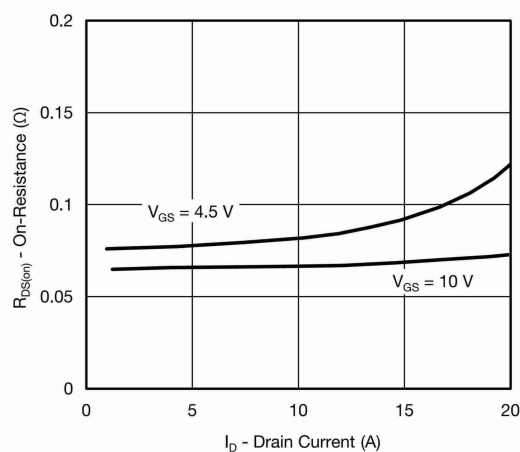
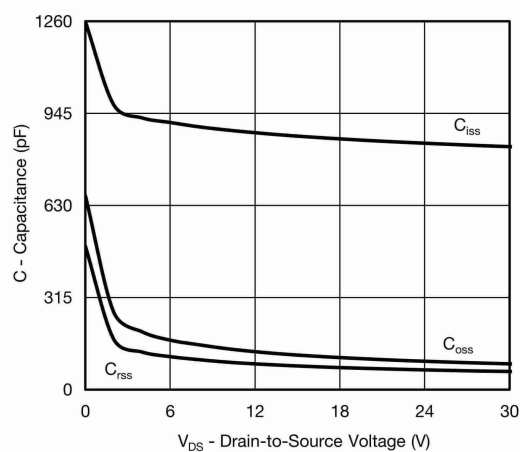
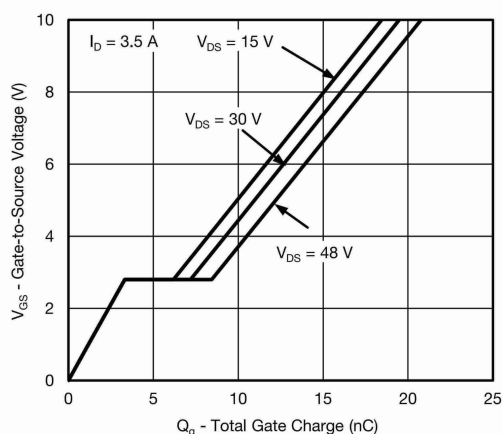
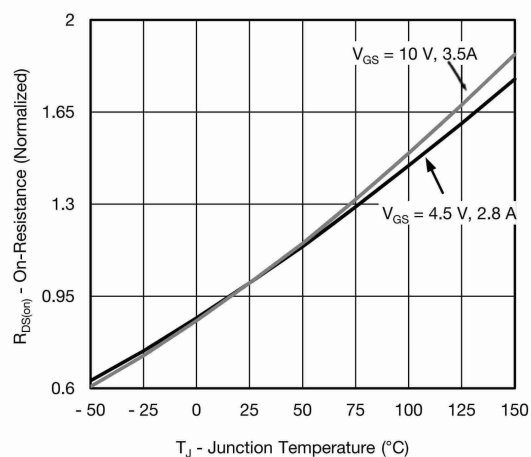
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 110 °C/W.
- Based on $T_C = 25$ °C.

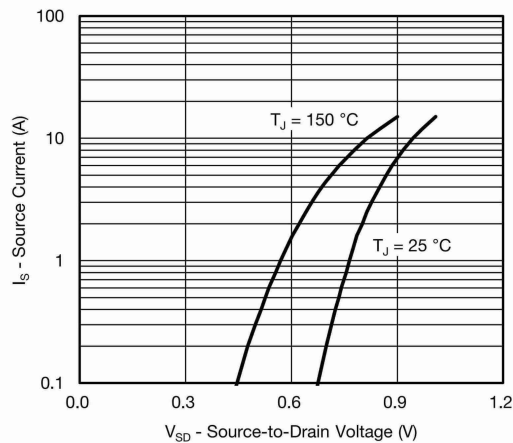
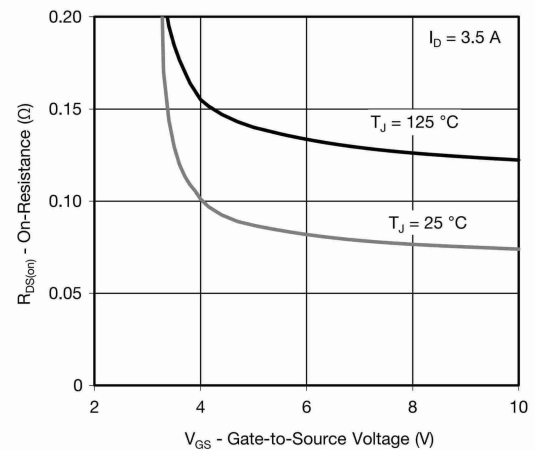
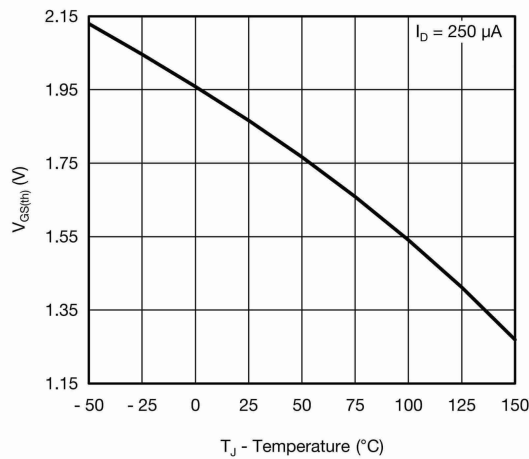
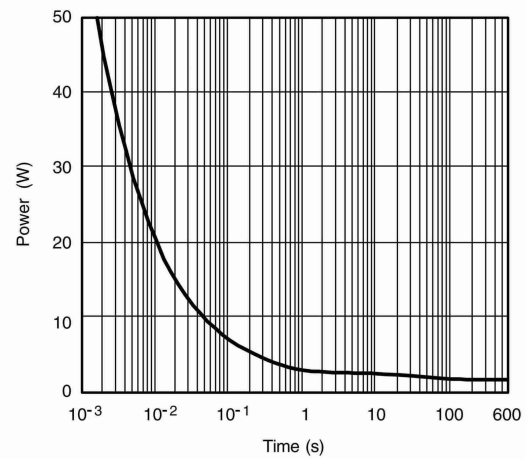
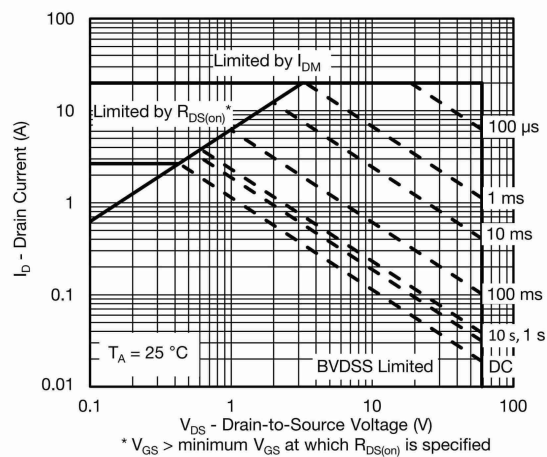
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-6.7	-	mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		-	4.3	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1	-	-3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ -10 V, V _{GS} = -10 V	-30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -3.5 A	-	0.070	-	Ω
		V _{GS} = -4.5 V, I _D = -2.8 A	-	0.085	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = -30 V, I _D = -3.5 A	-	11	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = -30 V, V _{GS} = 0 V, f = 1 MHz	-	832	-	pF
Output Capacitance	C _{oss}		-	88	-	
Reverse Transfer Capacitance	C _{rss}		-	63	-	
Total Gate Charge	Q _g	V _{DS} = -30 V, V _{GS} = -10 V, I _D = -3.5 A	-	20	30	nC
		V _{DS} = -30 V, V _{GS} = -4.5 V, I _D = -3.5 A	-	10.1	15.2	
Gate-Source Charge	Q _{gs}		-	3.3	-	
Gate-Drain Charge	Q _{gd}		-	3.9	-	
Gate Resistance	R _g	f = 1 MHz	1.8	9	18	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -10 V, R _g = 1 Ω	-	8	16	ns
Rise Time	t _r		-	6	12	
Turn-Off DelayTime	t _{d(off)}		-	35	53	
Fall Time	t _f		-	16	24	
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	40	60	
Rise Time	t _r		-	28	42	
Turn-Off DelayTime	t _{d(off)}		-	31	47	
Fall Time	t _f		-	15	23	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	-3.5	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}		-	-	-20	
Body Diode Voltage	V _{SD}	I _S = -2.8 A, V _{GS} = 0 V	-	-0.85	-1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = -2.8 A, dI/dt = 100 A/μs, T _J = 25 °C	-	32	48	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	45	68	nC
Reverse Recovery Fall Time	t _a		-	24	-	ns
Reverse Recovery Rise Time	t _b		-	8	-	

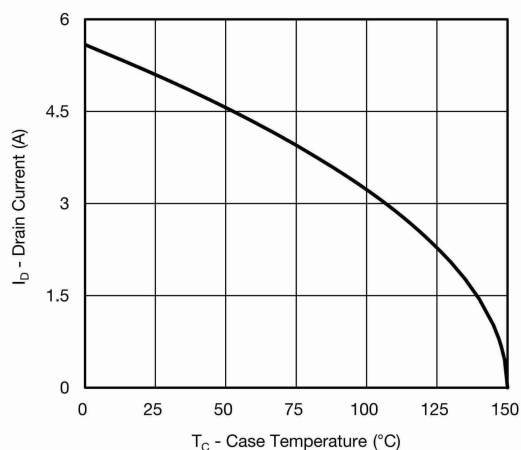
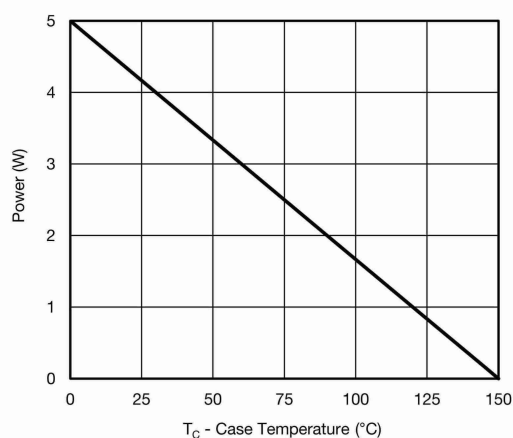
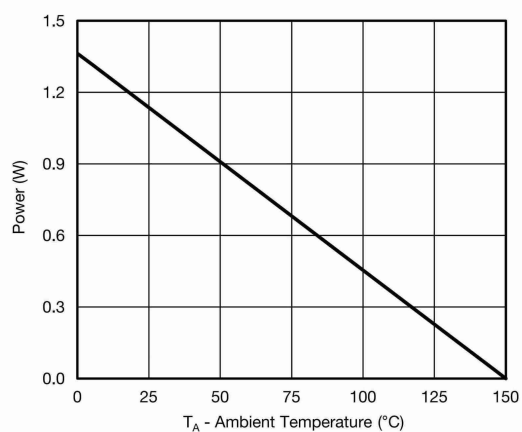
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

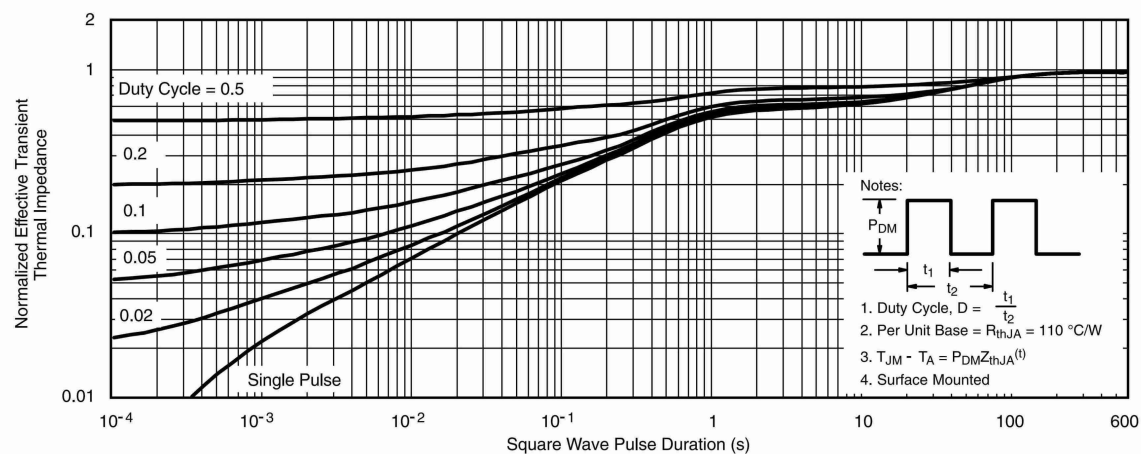
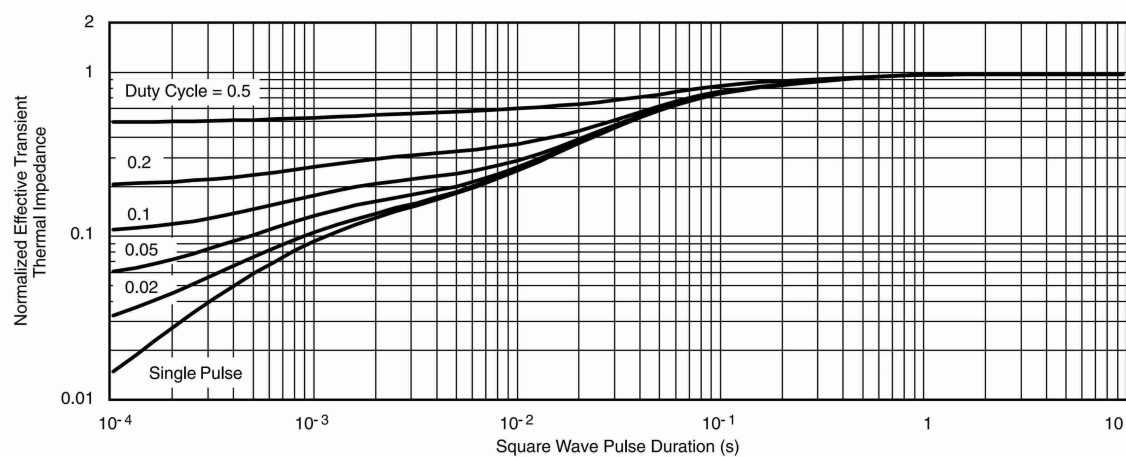
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

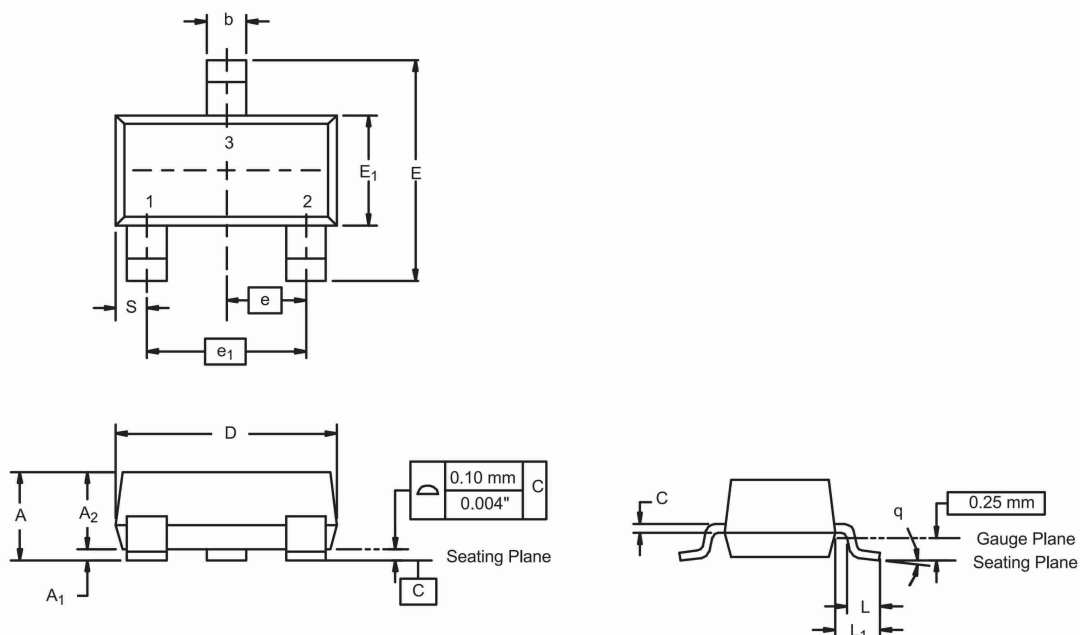
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Safe Operating Area**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Current Derating*****Power, Junction-to-Foot****Power Derating, Junction-to-Ambient**

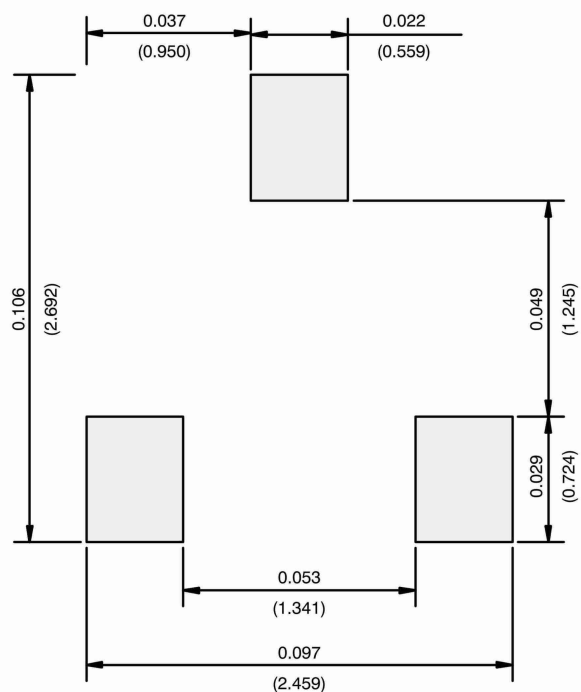
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

SOT-23 (TO-236): 3-LEAD

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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